

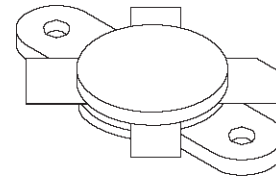
**SD2933****RF POWER TRANSISTORS
HF/VHF/UHF N-CHANNEL MOSFETs**

ADVANCE DATA

- GOLD METALLIZATION
- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 300\text{ W MIN. WITH } 20\text{ dB GAIN @ } 30\text{ MHz}$
- THERMALLY ENHANCED PACKAGING

DESCRIPTION

The SD2933 is a gold metallized N-Channel MOS field-effect RF power transistor. It is intended for use in 50 V DC large signal applications up to 150 MHz

**M177**

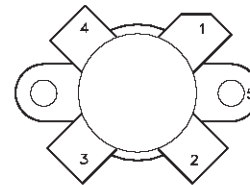
epoxy sealed

ORDER CODE

SD2933

BRANDING

SD2933

PIN CONNECTION

SC1424D

- | | |
|-----------|-----------|
| 1. Drain | 4. Source |
| 2. Source | 5. Source |
| 3. Gate | |

ABSOLUTE MAXIMUM RATINGS($T_{CASE} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain Source Volatage	125	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} = 1\text{M}\Omega$)	125	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	40	A
P_{DISS}	Power Dissipation	648	W
T_j	Max. Operating Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to 150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction-Case Thermal Resistance	0.27	$^{\circ}\text{C/W}$
$R_{th(c-s)}$	Case-Heatsink Thermal Resistance*	0.15	$^{\circ}\text{C/W}$

* Determined using a flat aluminum or copper heatsink with thermal compound applied (Dow Corning 340 or equivalent).

Jun 2000

1/8

ELECTRICAL SPECIFICATION(T_{CASE} = 25 °C)

STATIC

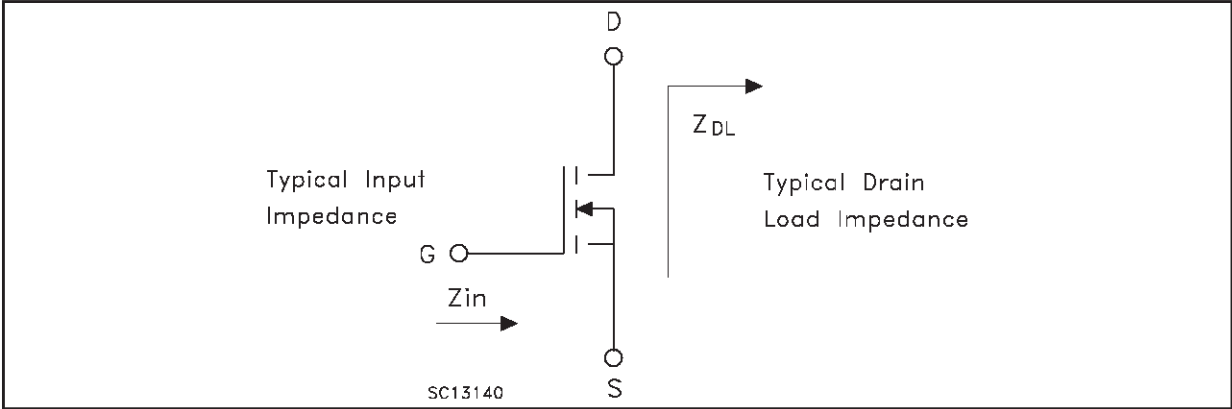
Symbol	Parameter		Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	I _{DS} = 200 mA	125			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 50 V			10	mA
I _{GSS}	V _{GS} = 20 V	V _{DS} = 0 V			10	μA
V _{GS(Q)}	V _{DS} = 10 V	I _D = 250 mA	2		5	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 10 A			3	V
g _{FS}	V _{DS} = 10 V	I _D = 10 A	10			mho
C _{ISS}	V _{GS} = 0 V	V _{DS} = 50 V		1000		pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 50 V		372		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 50 V		29		pF

REF. 7170198B

DYNAMIC

Symbol	Parameter		Min.	Typ.	Max.	Unit
P _{OUT}	f = 30 MHz	V _{DD} = 50 V I _{DQ} = 250 mA	300	400		W
G _{PS}	f = 30 MHz	V _{DD} = 50 V P _{OUT} = 300 W I _{DQ} = 250 mA	20	23.5		dB
η _D	f = 30 MHz	V _{DD} = 50 V P _{OUT} = 300 W I _{DQ} = 250 mA	50	65		%
Load Mismatch	f = 30 MHz All Phase Angles	V _{DD} = 50 V P _{OUT} = 300 W I _{DQ} = 250 mA	3:1			VSWR

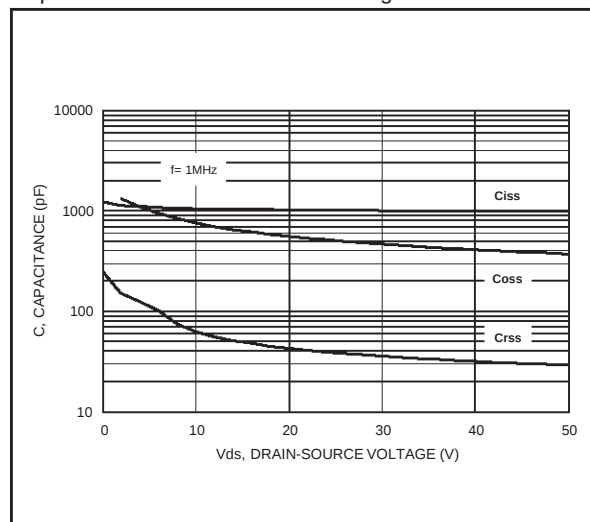
IMPEDANCE DATA



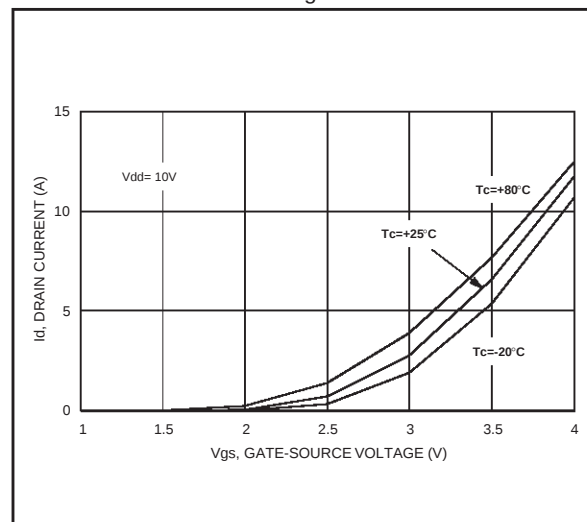
Frequency	Z _{IN} (Ω)	Z _{DL} (Ω)
30 MHz	1.8 - j 0.2	2.8 + j 2.3
108 MHz	1.9 + j 0.2	1.6 + j 1.4
150 MHz	1.9 + j 0.3	1.5 + j 1.6

TYPICAL PERFORMANCE

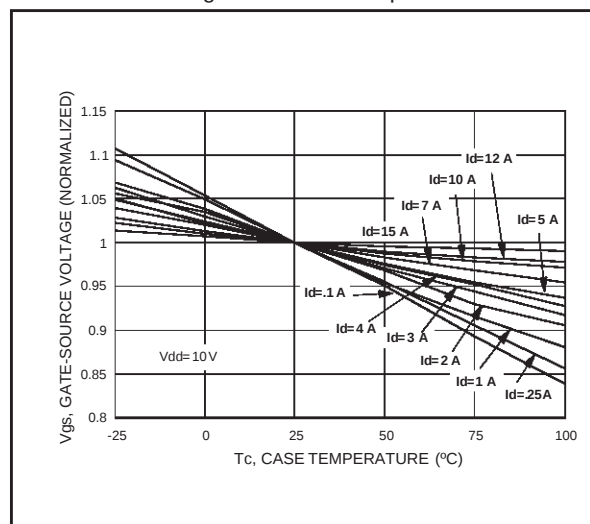
Capacitance vs. Drain-Source Voltage



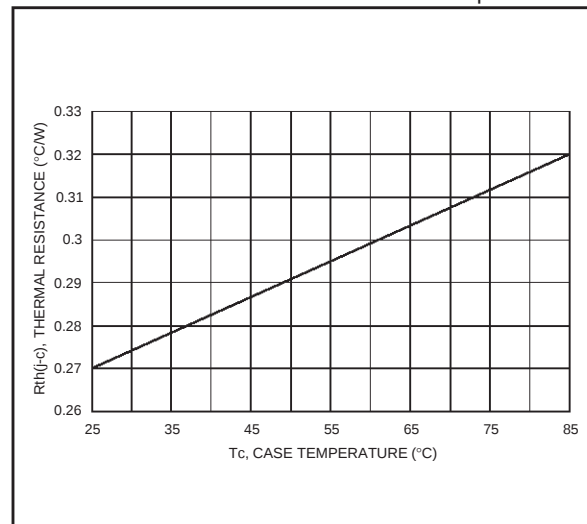
Drain Current vs. Gate Voltage



Gate-Source Voltages vs. Case Temperature

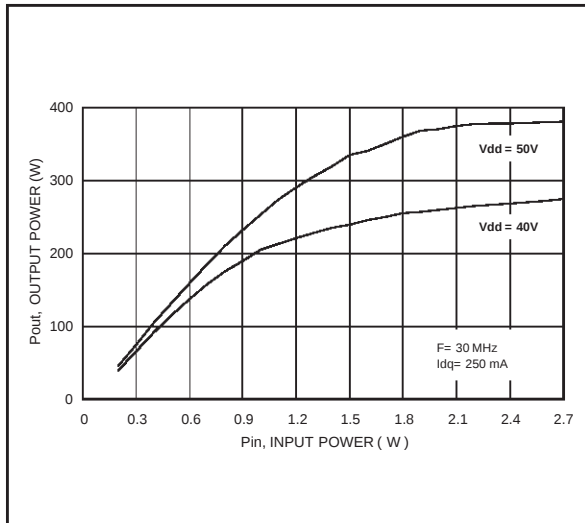


Maximum Thermal Resistance vs. Case Temperature

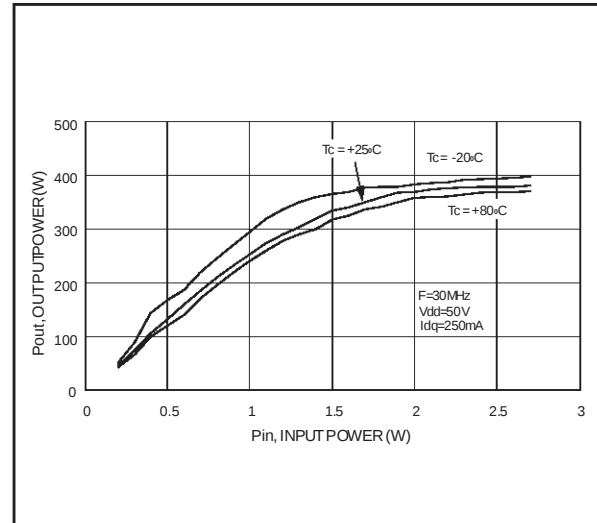


TYPICAL PERFORMANCE

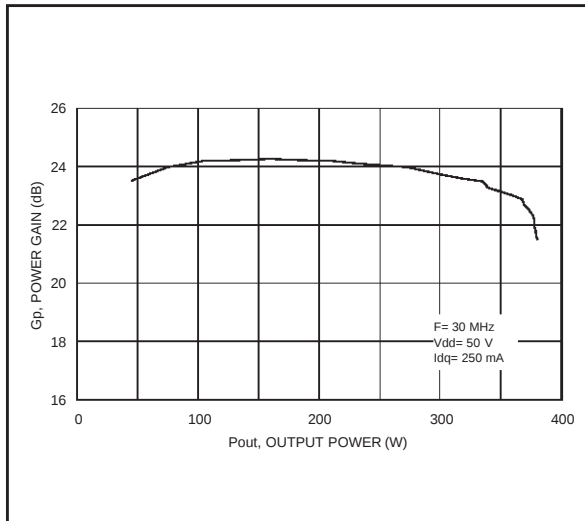
Output Power vs. Input Power



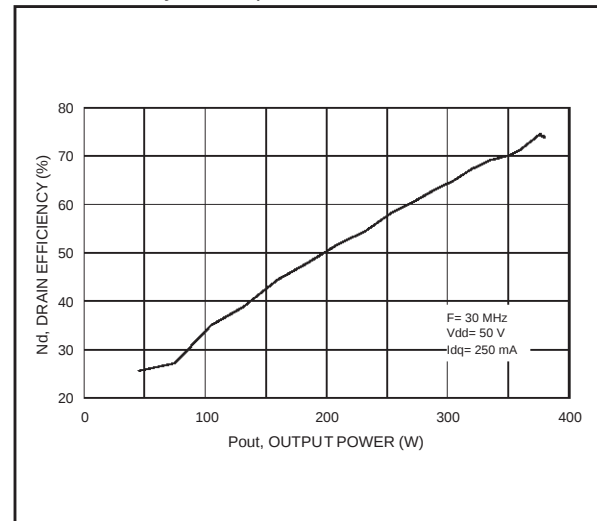
Output Power vs. Input Power



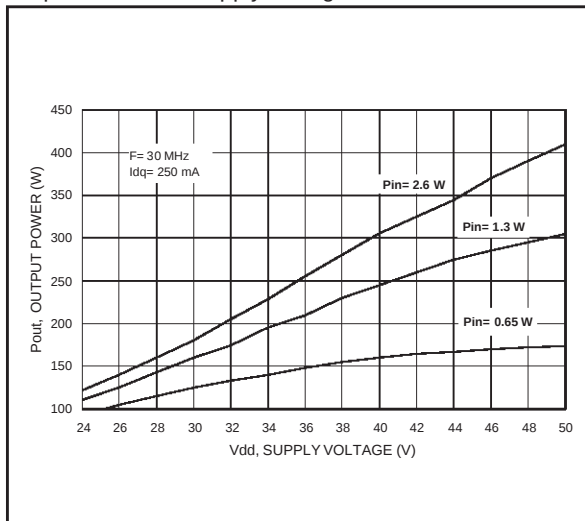
Power Gain vs. Output Power



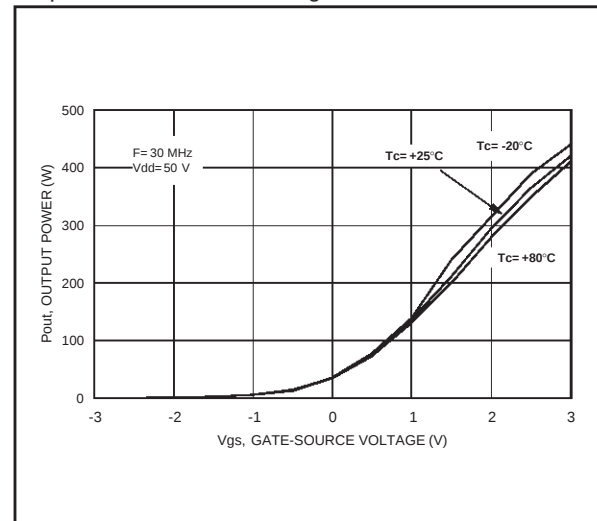
Drain Efficiency vs. Output Power



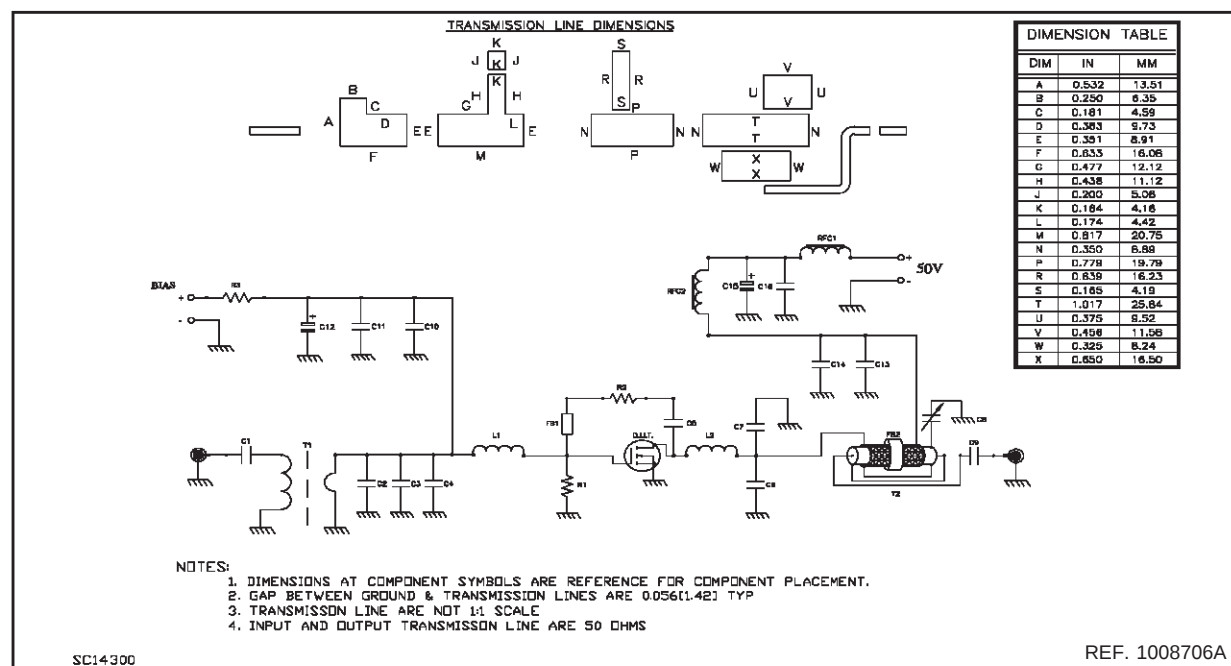
Output Power vs. Supply Voltage



Output Power vs. Gate Voltage



30 MHZ TEST CIRCUIT SCHEMATIC



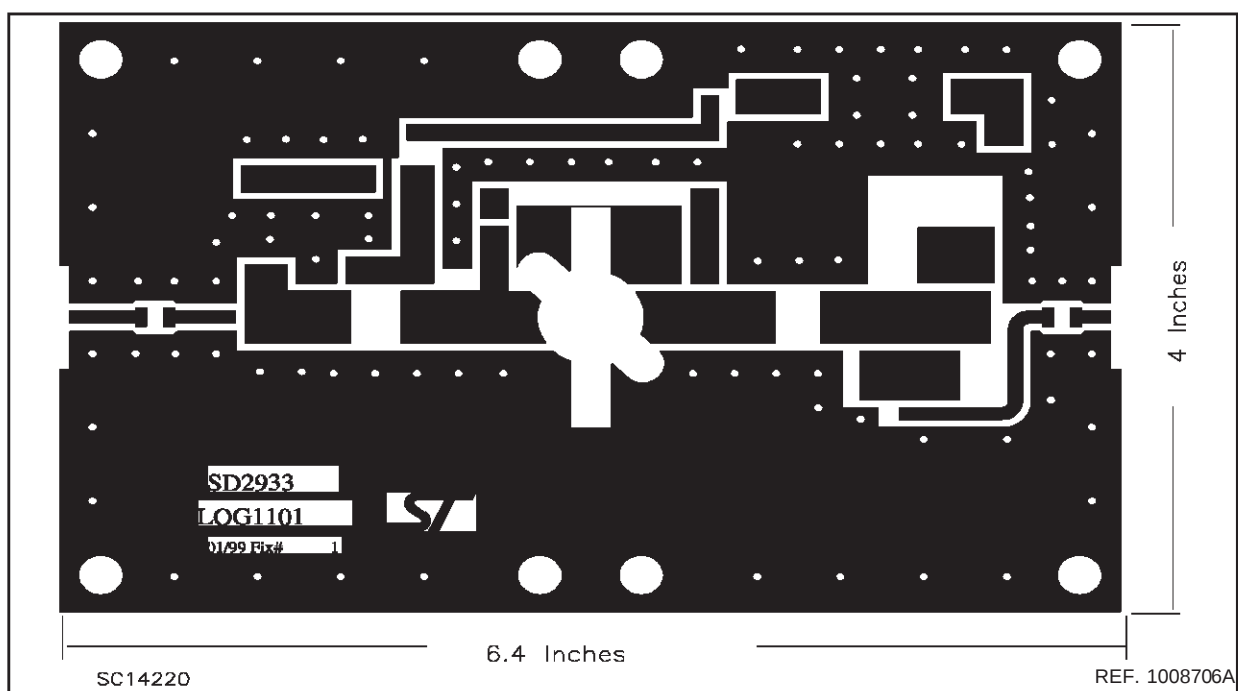
30 MHz TEST CIRCUIT COMPONENT PART LIST

C16	ATC200B103MW50X	ATC	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C15	SKR101M1JC13V7	MALLORY	100 μ F / 63V ALUMINUM ELECTROLYTICS RADIAL LEAD CAPACITOR
C14	ATC200B103MW50X	ATC	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C13	ATC700B122MW50X	ATC	1200 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C12	SKR470M1JF11V	MALLORY	47 μ F / 63V ALUMINUM ELECTROLYTICS RADIAL LEAD CAPACITOR
C11	ATC200B103MW50X	ATC	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C10	ATC200B103MW50X	ATC	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C9	C1812X7R501-103KNE	VENKEL	0.01 μ F / 500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C8	TYPE 468	ARCO	175-680 pF TYPE 46 STANDARD TRIMMER CAPACITOR
C7	ATC700B301JP200X	ATC	300 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C6	ATC700B511MW100X	ATC	510 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C5	ATC200B103MW50X	ATC	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C4	ATC700B301JP200X	ATC	300 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C3	ATC700B751MW50X	ATC	750 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C2	ATC700B751MW50X	ATC	750 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C1	C1812X7R501-103KNE	VENKEL	0.01 μ F / 500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
R3	CR2512-1W-102JB	VENKEL	1 K OHM 1 W SURFACE MOUNT CHIP RESISTOR
R2	RS-2B	DALE	560 OHM 2 W WIRE-WOUND AXIAL LEAD RESISTOR
R1	CR2512-1W-102JB	VENKEL	1 K OHM 1 W SURFACE MOUNT CHIP RESISTOR
T2	83242	BELDEN	RG-142B/U 50 OHM COAXIAL CABLE OD = 0.165[4.18] L=15'[381.00] COVERED - WITH 15'[381.00] TINNED COPPER TUBULAR BRAID 13/65[5.1] WIDTH
T1	RT-600-9	COMM CONCEPTS, Inc	HF 2-30 MHZ SURFACE MOUNT 9:1 (Impedance Ratio) TRANSFORMER (43 Material)
L2	TYPE 8011	BELDEN	1 3/4 TURN AIR-WOUND 12AWG ID=0.250[6.34] BUS BAR WIRE
L1	TYPE 8074	BELDEN	1 3/4 TURN AIR-WOUND 16AWG ID=0.219[5.56] POLY-COATED MAGNET WIRE
RFC2	2643801102	FAIR-RITE CORP	3 TURNS 14AWG WIRE THROUGH FAIR RITE TOROID
RFC1	2643801102	FAIR-RITE CORP	3 TURNS 14AWG WIRE THROUGH FAIR RITE TOROID
FB2	5967002701	FAIR-RITE CORP	TOROID
FB1	2743019447	FAIR-RITE CORP	SURFACE MOUNT EMI SHIELD BEAD
PCB	GO300M10260B	ROGERS CORP.	ULTRALAM 2000. 0.030 THK, $\epsilon_r = 2.55$, 2 Oz ED CU BOTH SIDES
COMPONENT	PART N.	VENDOR	DESCRIPTION

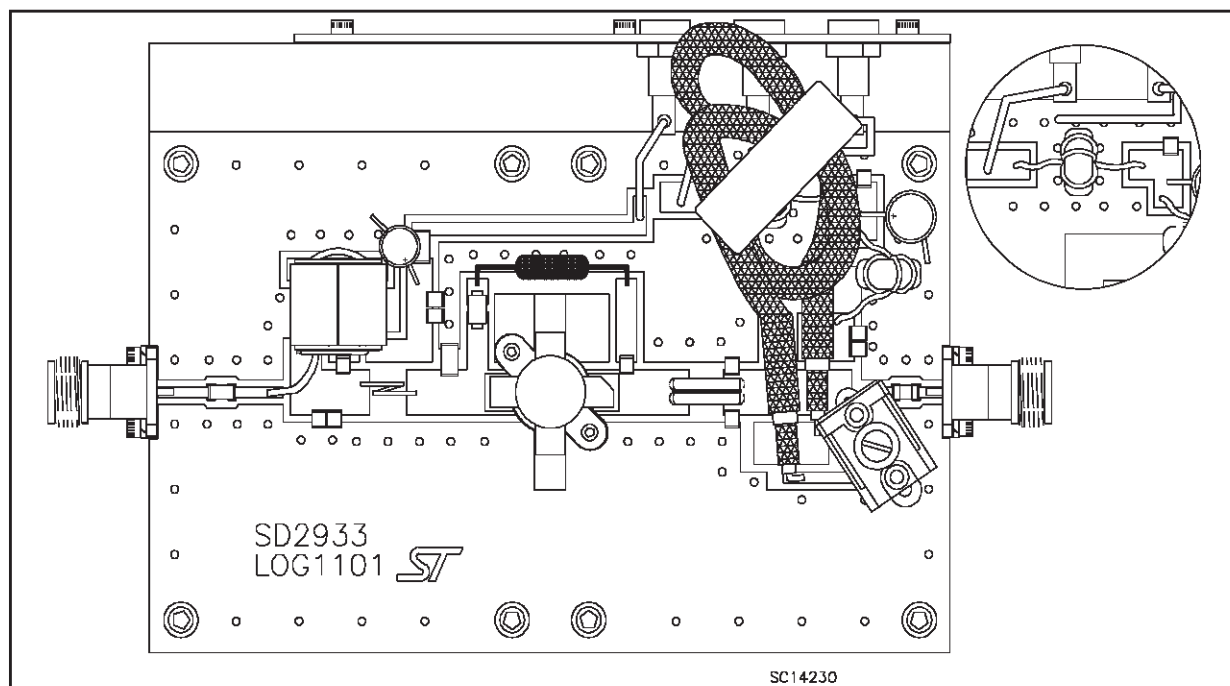
SC14210

SD2933

30 MHZ TEST CIRCUIT PHOTOMASTER

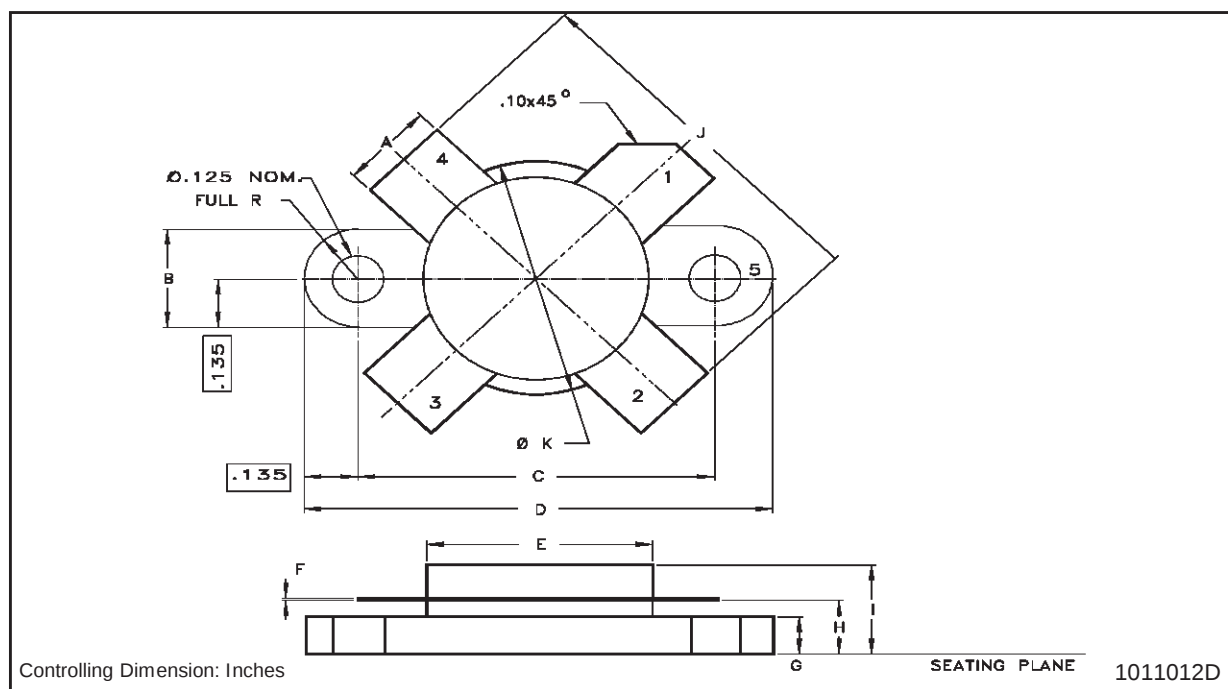


30 MHZ PRODUCTION TEST FIXTURE



M177 (.550 DIA. 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	5.72		5.97	0.225		0.235
B	6.73		6.96	0.265		0.275
C	21.84		22.10	0.860		0.870
D	28.70		28.96	1.130		1.140
E	13.84		14.10	0.545		0.555
F	0.08		0.18	0.003		0.007
G	2.49		2.74	0.098		0.108
H	3.81		4.32	0.150		0.170
I			7.11			0.280
J	27.43		28.45	1.080		1.120
K	15.88		16.13	0.625		0.635



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